

To all our customers

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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

Cautions

Keep safety first in your circuit designs!

1. Renesas Technology Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage.

Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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H5N2510DL, H5N2510DS

Silicon N Channel MOS FET
High Speed Power Switching

RENESAS

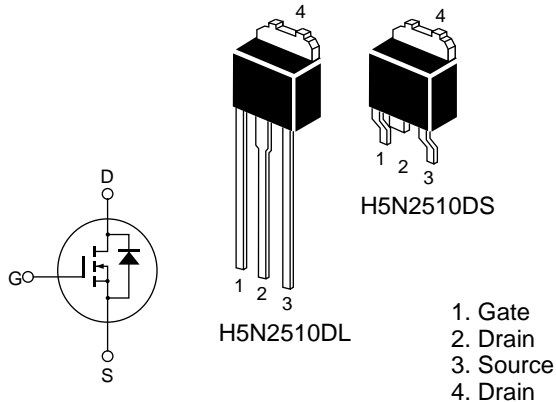
ADE-208-1379 (Z)
Target Specification 1st. Edition
Mar. 2001

Features

- Low on-resistance
- Low drive current
- High speed switching

Outline

DPAK-2



H5N2510DL, H5N2510DS

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	250	V
Gate to source voltage	V_{GSS}	±20	V
Drain current	I_D	(5)	A
Drain peak current	$I_{D (pulse)}^{Note1}$	(20)	A
Body-drain diode reverse drain current	I_{DR}	(5)	A
Body-drain diode reverse drain peak current	$I_{DR (pulse)}^{Note1}$	(20)	A
Channel dissipation	P_{ch}^{Note2}	25	W
Channel to case Thermal Impedance	θ_{ch-c}	5	°C/W
Channel temperature	T_{ch}	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

Notes: 1. $PW \leq 10 \mu s$, duty cycle $\leq 1\%$
2. Value at $T_c = 25^\circ C$

Electrical Characteristics (Ta = 25°C)

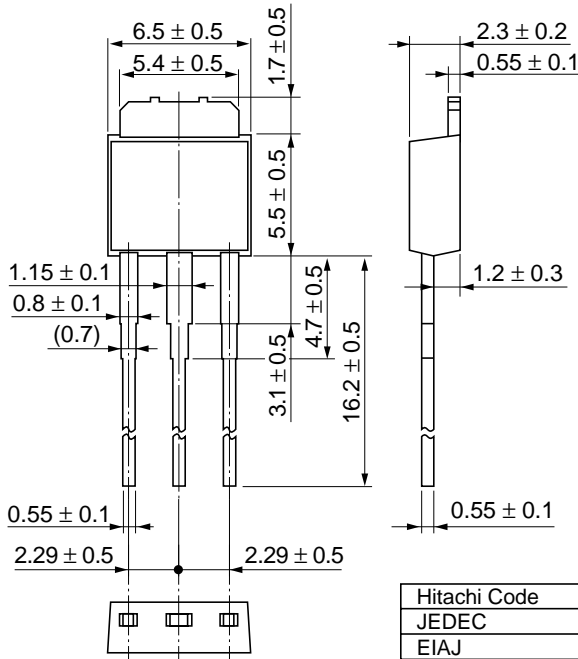
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	250	—	—	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source leak current	I_{GSS}	—	—	± 0.1	μA	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	1	μA	$V_{DS} = 250 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	(1.0)	—	(2.5)	V	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$
Static drain to source on state resistance	$R_{DS(on)}$	—	(0.68)	(0.89)	Ω	$I_D = 2.5 \text{ A}, V_{GS} = 10 \text{ V}$ ^{Note4}
	$R_{DS(on)}$	—	(0.72)	(0.97)	Ω	$I_D = 2.5 \text{ A}, V_{GS} = 10 \text{ V}$ ^{Note4}
Forward transfer admittance	$ y_{fs} $	(3.2)	(5.3)	—	S	$I_D = 2.5 \text{ A}, V_{DS} = 4 \text{ V}$ ^{Note4}
Input capacitance	C_{iss}	—	(390)	—	pF	$V_{DS} = 25 \text{ V}$
Output capacitance	C_{oss}	—	(45)	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	C_{rss}	—	(13)	—	pF	$f = 1 \text{ MHz}$
Total gate charge	Q_g	—	(15.2)	—	nC	$V_{DD} = 200 \text{ V}$
Gate to source charge	Q_{gs}	—	(1.3)	—	nC	$V_{GS} = 10 \text{ V}$
Gate to drain charge	Q_{gd}	—	(5.1)	—	nC	$I_D = 5 \text{ A}$
Turn-on delay time	$t_{d(on)}$	—	(12)	—	ns	$I_D = 2.5 \text{ A}$
Rise time	t_r	—	(14)	—	ns	$V_{GS} = 10 \text{ V}$
Turn-off delay time	$t_{d(off)}$	—	(66)	—	ns	$R_L = 50 \Omega$
Fall time	t_f	—	(11)	—	ns	$R_g = 10 \Omega$
Body-drain diode forward voltage	V_{DF}	—	(1.0)	(1.5)	V	$I_F = 5 \text{ A}, V_{GS} = 0$
Body-drain diode reverse recovery time	t_{rr}	—	(100)	—	ns	$I_F = 5 \text{ A}, V_{GS} = 0$
Body-drain diode reverse recovery charge	Q_{rr}	—	(320)	—	nC	$diF/dt = 100 \text{ A}/\mu\text{s}$

Note: 4. Pulse test

Package Dimensions

As of January, 2001

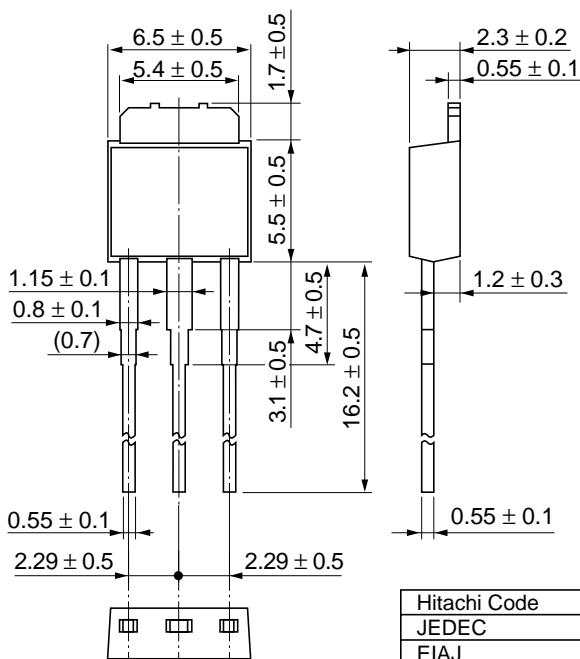
Unit: mm



Hitachi Code	DPAK (L)-(2)
JEDEC	—
EIAJ	—
Mass (reference value)	0.42 g

As of January, 2001

Unit: mm

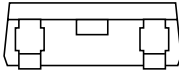
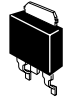
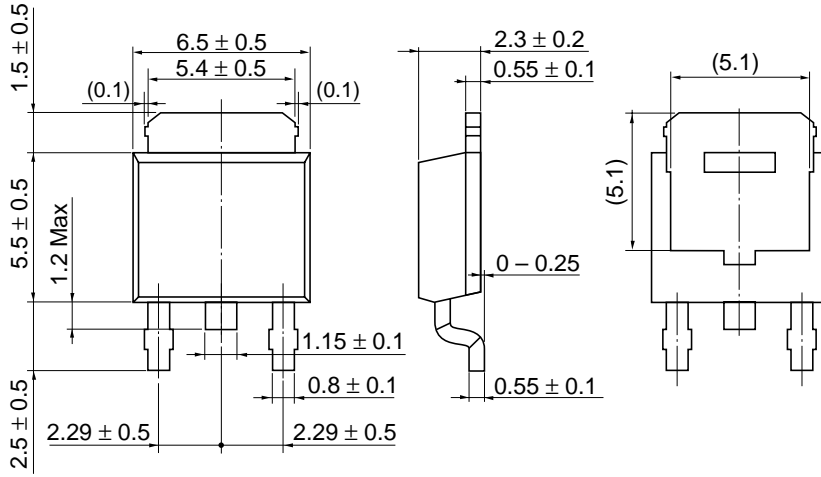


Hitachi Code	DPAK (L)-(2)
JEDEC	—
EIAJ	—
Mass (reference value)	0.42 g

H5N2510DL, H5N2510DS

As of January, 2001

Unit: mm



Hitachi Code	DPAK (S)-(3)
JEDEC	—
EIAJ	Conforms
Mass (reference value)	0.28 g

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HITACHI

Hitachi, Ltd.

Semiconductor & Integrated Circuits.

Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL NorthAmerica : <http://semiconductor.hitachi.com/>
 Europe : <http://www.hitachi-eu.com/hel/ecg>
 Asia : <http://sicapac.hitachi-asia.com>
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For further information write to:

Hitachi Semiconductor
 (America) Inc.
 179 East Tasman Drive,
 San Jose, CA 95134
 Tel: <1> (408) 433-1990
 Fax: <1> (408) 433-0223

Hitachi Europe GmbH
 Electronic Components Group
 Dornacher Straße 3
 D-85622 Feldkirchen, Munich
 Germany
 Tel: <49> (89) 9 9180-0
 Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.
 Electronic Components Group.
 Whitebrook Park
 Lower Cookham Road
 Maidenhead
 Berkshire SL6 8YA, United Kingdom
 Tel: <44> (1628) 585000
 Fax: <44> (1628) 585160

Hitachi Asia Ltd.
 Hitachi Tower
 16 Collyer Quay #20-00,
 Singapore 049318
 Tel : <65>-538-6533/538-8577
 Fax : <65>-538-6933/538-3877
 URL : <http://www.hitachi.com.sg>

Hitachi Asia Ltd.
 (Taipei Branch Office)
 4/F, No. 167, Tun Hwa North Road,
 Hung-Kuo Building,
 Taipei (105), Taiwan
 Tel : <886>-(2)-2718-3666
 Fax : <886>-(2)-2718-8180
 Telex : 23222 HAS-TP
 URL : <http://www.hitachi.com.tw>

Hitachi Asia (Hong Kong) Ltd.
 Group III (Electronic Components)
 7/F., North Tower,
 World Finance Centre,
 Harbour City, Canton Road
 Tsim Sha Tsui, Kowloon,
 Hong Kong
 Tel : <852>-(2)-735-9218
 Fax : <852>-(2)-730-0281
 URL : <http://www.hitachi.com.hk>

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